

3.6*3.6mm Si PIN Module

Features

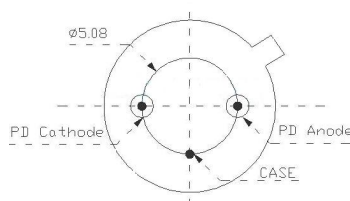
- plane structure
- low dark current
- high responsivity
- high reliability

Applications

Photoelectric conversion system
in the wavelength range of 350-1100nm



PIN assignment



This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures



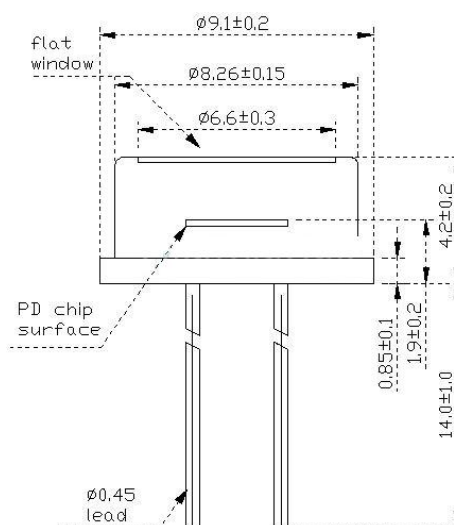
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Storage temperature	T _{st}	-40~+85	°C
Operating temperature	T _{op}	-40~+85	°C
Reverse voltage	V _R	30	V
Soldering temperature/time	—	260/10	°C/ s

Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Detection range	λ	350	-	1100	nm	-
Dark current	I _d	-	20	10	PA	V _R =10mV
Quantum efficiency	R	-	0.20	-	A/W	V _R =10mV, λ =632.8nm
		-	0.35	-		V _R =10mV, λ =530nm
		-	0.50	-		V _R =10mV, λ =900nm
		-	0.52	-		V _R =10mV, λ =940nm
Rise/fall time	Tr/f	-	10	-	ns	10%~90%
Capacitance	C _t	-	1300	0.75	pF	f=1MHz, V _R =0V
Noise equivalent power	NEP		1.5×10 ⁻¹⁵			W/Hz ^{1/2}

Dimensions Diagram



Order information

SPD1	4	2
	Active area	Package
	1:0.5mm	1, TO-46
	2:1mm	2, TO-5
	3,2mm	
	4,3.6*3.6	